# THE UNITED STATES PATENT AND TRADEMARK OFFICE

Application Serial No	09/652,550
Filing Date	August 31, 2000
Inventor	Keiji Jono et al.
Assignee	Micron Technology, Inc.
Group Art Unit	2811
Examiner	Quang D. Vu
Attorney's Docket No	KM1-001
Title Methods of Forming an Isolati	ion Trench in a Semiconductor,
Methods of Forming an Isolation Trench in a Sur	face of a Silicon Wafer, Methods
of Forming an Isolation Trench-Isolated Transis	stor, Trench-Isolated Transistor,
Trench Isolation Structures Formed in a Sem	iconductor, Memory Cells and
DRAMS	

### SUPPLEMENTAL INFORMATION DISCLOSURE STATEMENT

References -- See Attached Form PTO-1449

The attached form PTO-1449 is submitted in compliance with 37 CFR §1.56. Copies of the cited art are included. No admission is made regarding whether all the submitted references are prior art.

Respectfully submitted,

Dated: 6-30-04

Mark S. Matkin Reg. No. 32,268

, w, U.S. DEPARTMENT OF COMMERCE ATTY. DOCKET NO. Form PTO-1449 SERIAL NO. PATENT AND TRADEMARK OFFICE KM1-001 09/652,550 LIST OF ART CITED BY APPLICANT APPLICANT: Keiji Jono et al. (Use several sheets if necessary) FILING DATE GROUP August 31, 2000 2811 **U.S. PATENT DOCUMENTS** Class Subclass Filing Date Date \*Examiner's Document Name Number If Appropriate Initials AA 5,915,191 06/1999 Jun 438 431 AB 07/2000 Gardner et al. 257 510 6,087,705 6,355,540 B1 03/2002 Wu 438 433 ΑD ΑE AG AH FOREIGN PATENT DOCUMENTS Date Translation Document Country Number Yes No AJ AL OTHER REFERENCES (including Author, Title, Date, Pertinent Pages, Etc.) **EXAMINER** DATE CONSIDERED \*EXAMINER: Initial if reference considered, whether or not citation is in conformance with MPEP 609; Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.



# EL979953133

### HE UNITED STATES PATENT AND TRADEMARK OFFICE

	August 31, 2000
	Keiji Jono et al.
Assignee	KMT Semiconductor, LTD and Micron Technology, Inc.
Group Art Unit	
	Quang D. Vu
Attorney's Docket No	KM1-001
Title: Methods of Forming	an Isolation Trench in a Semiconductor, Methods of
Forming an Isolation	Trench in a Surface of a Silicon Wafer, Methods of
Forming an Isolation <sup>1</sup>	Trench-Isolated Transistor, Trench-Isolated Transistor,
Trench Isolation Struc	ctures Formed in a Semiconductor, Memory Cells and
DRAMS	

## SUPPLEMENTAL INFORMATION DISCLOSURE STATEMENT

References - See Attached Form PTO-1449

The Examiner's attention is directed to the references which are listed on the attached Form PTO-1449, copies of which are attached. No admission is made regarding whether all the submitted references are prior art.

Citation of the referenced art is respectfully requested.

Respectfully submitted,

Dated: 2-2-04

D. Brent Kenady

Reg. No. 40,045

Form PTO-1449 U.S. DEPARTMENT OF COMMERCE SERIAL NO. ATTY, DOCKET NO. PATENT AND TRADEMARK OFFICE KM1-001 09/652,550 LIST OF ART CITED BY APPLICANT (Use several sheets if necessary) APPLICANT: Keiji Jono et al. FILING DATE **GROUP** August 31, 2000 2811 U.S. PATENT DOCUMENTS \*Examiner Document Date Name Class Subclass Filing Date
If Appropriate Initial Number 6,081,662 06/27/00 Murakami et al. ΑB 5,994,198 11/30/99 Hsu et al. AC AD ΑE AF AG AΗ ΑJ ΑK FOREIGN PATENT DOCUMENTS Document Date Country Class Number Yes No AM AN AO AΡ OTHER REFERENCES (including Author, Title, Date, Pertinent Pages, Etc.) AR AS **EXAMINER** DATE CONSIDERED

\*EXAMINER: Initial if reference considered, whether or not citation is in conformance with MPEP 609; Draw line through citation if not in

conformance and not considered. Include copy of this form with next communication to applicant,

EV372458831

# INCHE UNITED STATES PATENT AND TRADEMARK OFFICE Application Serial No. 09/652,550 Filing Date August 31, 2000 Inventor Keiji Jono et al. Assignee KMT Semiconductor, LTD Group Art Unit 2811 Examiner Quang D. Vu Attorney's Docket No. KM1-001 Title: Methods of Forming an Isolation Trench in a Semiconductor, Methods of Forming an Isolation Trench in a Surface of a Silicon Wafer, Methods of Forming an Isolation Trench-Isolated Transistor, Trench-Isolated Transistor, Trench Isolation Structures Formed in a Semiconductor, Memory Cells and DRAMS

SUPPLEMENTAL INFORMATION DISCLOSURE STATEMENT

References - See Attached Form PTO-1449

The Examiner's attention is directed to the references which are listed on the attached Form PTO-1449, copies of which are attached. No admission is made regarding whether all the submitted references are prior art.

Citation of the referenced art is respectfully requested.

Respectfully submitted,

Dated:  $3 - (0 - 0)^3$ 

Bv:

D. Brent Kenady Reg. No. 40,045

Form PTC	U.S. DEPARTMENT OF COMMERCE PATENT AND TRADEMARK OFFICE		ATTY. DOCKET NO. KM1-001		SER 09/6	SERIAL NO. 09/652,550			
	PE (Use several sheets if necessary)			APPLICANT: Keiji Jono et al.					
(Use several sheets if necessary)			FILING DATE August 31, 2000			GROUP 2811			
U.S. PATENT DOCUMENTS									
*Examiner Initial		Document Number	Date	Name		Class	Subclass	Filing Date If Appropriate	
	AA	6,034,409	03/07/2000	Sakai et al.					
	AB	6,171,924 B1	01/09/2001	Wang et al.					
	AC	6,154,417	11/28/2000	Kim					
	AD								
	AE								
	AF					<u> </u>			
	AG		<u> </u>						
	АН							ļ	
	AI -		<u> </u>			<u> </u>		· •	
	7								
	AK	_							
			FOR	EIGN PATENT DOCUM		T	I		
		Document Number	Date Country	Country	,	Class	Subclass	Translation	
	AL							Yes No	,
	АМ								
	AN								$\dashv$
	AO AP			<u>-</u>	- <del>1 1 </del>				$\exists$
		OTHER REF	ERENCES (i	ncluding Author, Title, C	ate, Pertinent F	ages, Etc	.)		
	AR								
			***************************************						
``	AS								
				- 17	· · · · · · · · · · · · · · · · · · ·				
	AT				· · · · · · · · · · · · · · · · · · ·				
								<del>V</del>	
EXAMINER	·			DATE CONSID	ERED <sup>.</sup>				
*EXAMINER: Initial if reference considered, whether or not citation is in conformance with MPEP 609; Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.									

EV372458831